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## M agnetotherm opower and m agnon-assisted transport in ferrom agnetic tunnel junctions

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We present a model of the therm opower in a mesoscopic tunnel junction between two ferromagnetic metals based upon magnon-assisted tunneling processes. In our model, the therm opower is generated in the course of thermal equilibration between two baths of magnons, mediated by electrons. We predict a particularly large thermopowere ect in the case of a junction between two half-metallic ferromagnets with antiparallel polarizations,  $S_{A\,P}$  ( $k_B$  =e), in contrast to  $S_P$  0 for a parallel conguration.

Spin valve systems and magnetic multilayers displaying giant magnetoresistance e ects also exhibit substantial magnetothermopower<sup>1 { 6</sup> with a strong temperature dependence. In metals, the therm opower S is related to the conductivity of electrons taken at a certain energy, (), by the Mott formula, S =(  ${}^2k_{\rm B}^2$  T=3e) (0 ln ( )=0 ), so that it typically contains a small parameter such as  $k_B T = F$ . Theories of transport in magnetic multilayers with highly transparent interfaces based upon the use of the Mott formula have explained the di erence between therm opower in the parallel (P) and anti-parallel (AP) con guration of ferrom agnetic layers as due to either the dierence in the energy dependence of the density of states for majority and m inority spin bands in ferrom agnetic layers, 8;9 or a di erent e ciency of electron-magnon scattering for carriers in opposite spin states.3 In particular, the electronm agnon interaction in a ferrom agnetic layer was incorporated to explain the observation<sup>3</sup> of a strong tem perature dependence of S (T) and gave, theoretically, a much larger therm opower in the parallel con quration of multilayers

with highly transparent interfaces than in the antiparallel

In this paper we investigate a model of the electronmagnon interaction assisted thermopower in a mesoscopic size ferrom agnet/insulator/ferrom agnet tunnel junction, which yields a di erent prediction. In the model we study below, the bottle-neck of both charge and heat transport lies in a small-area tunnel contact between ferrom agnetic metals held at dierent temperatures, T T=2. The therm opower is generated in the course of them al equilibration between two baths of magnons, mediated by electrons. We nd that the magnetothermopowere ect is most pronounced in the case of half-m etallic ferrom agnets, where the exchange spin splitting between the majority and minority conduction bands is greater than the Ferm i energy  $_{\rm F}$  m easured from the bottom of the majority band, and the Ferm idensity of states in the m inority band is zero. In a highly resistive antiparallel con quration of such a junction, where the emission/absorption of a magnon would lift the spin-blockade of electronic transfer between ferrom agnetic m etals, we predict a large therm opower effect, whereas in the lower-resistance parallel conguration them opower appears to be relatively weak:

$$S_{AP}$$
 0:64  $\frac{k_B}{e}$ ;  $\frac{S_P}{S_{AP}}$   $\frac{k_B T}{F}$ : (1)

We also found that for a junction between two conventional ferrom agnetic metals, the ability of electronic transfer assisted by magnon emission/absorption to create therm opower depends on the dierence between the size of majority/minority band Fermi surfaces and it is reduced by a temperature dependent factor g(T)  $(k_B T = !_D)^{3=2}$ . The latter rejects the fractional change in the net magnetization of the reservoirs due to thermal magnons (B loch's T  $^{3=2}$  law).

Below, we describe the calculation of the therm opower for the case of a tunnel contact between two half-metallic ferrom agnets and, then, we present its generalization to conventional ferrom agnetic metals. We obtain an expression for the current I (V; T) between bulk ferrom agnetic reservoirs, as a function of bias voltage, V, and of the temperature drop, T, and, then, determine the thermopower coecient S = V = T by satisfying the relation I (V; T) = 0. The expression for the current was derived using the balance equation, which takes into account competing elastic and inelastic electron transfer processes across the tunnel junction.

Let us consider, rst, the AP con guration of ferromagnetic electrodes, with spin-" majority electrons on the left hand side of the junction and spin-# on the right. For such an alignment, elastic tunneling of carriers between electrodes is blocked by the absence of available states for a spin-polarized electron on the other side of an insulating barrier, whereas electron transferm ay happen via tunneling processes assisted by a simultaneous em ission/absorption of a magnon. Since tails of wavefunctions of majority-spin (") electrons close to the Fermi level on the left hand side penetrate into the forbidden region on the right, an electron on one side of the junction acquires a weak coupling with core magnetic moments (and, therefore, magnons) on the other side. A characteristic event can be viewed as a two-step quantum process. First, an electron tunnels into a virtual interm ediate high-energy state in the m inority band. Then,

it incorporates itself into the majority band by ipping spin in a magnon-em ission process. Following the tunneling Ham iltonian approach, the amplitude for a spin-delectron with wave number k on the left to nish in a state (#; $k^0$ ) on the right after em itting a spin-wave with wavenumber q can be estimated using second order perturbation theory with respect to the electron -magnon interaction and the tunneling matrix element  $t_k$ ; $k^0$ +q:

$$A_{k;k^{0}+q} = \frac{t_{k;k^{0}+q}}{2 N (+_{k^{0}+q})} \frac{t_{k;k^{0}+q}}{2 N }; \qquad (2)$$

For  $k_B$  T;eV , when both initial and nalelectron states should be taken close to the Ferm i level, only long wavelength magnons can be emitted, so that the energy de cit in the virtual states can be approximated as +  $k^0+q$  k. As noticed in Refs. 10,12, this cancels out the large exchange parameter since the same electron-core spin exchange constant appears both in the splitting between minority and majority bands and in the electron-magnon coupling. [The number of localized moments in a ferromagnet N appears in Eq. (2) as we normalize both electron and magnon plane waves to the system volume, and is spin per unit magnetic cell.]

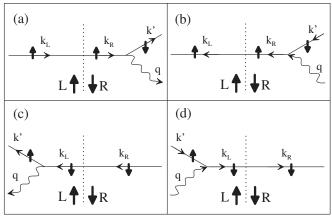


FIG. 1. Schem atic ofm agnon-assisted tunneling across a junction with half-metallic electrodes in the antiparallel conguration. Four processes which, to lowest order in the electron-magnon interaction, contribute to magnon-assisted tunneling. (a) and (c) involve magnonemission on the right and left hand sides, respectively, whereas (b) and (d) involve magnon absorption on the right and left.

To complete the balance equation describing electron transfer between halfm etallic electrodes, one has to take into account four magnon-assisted tunneling processes depicted in Figure 1. Below, we describe them in detail assuming that the tunnel barrier is at, so that the parallel component of the electron momentum conserves upon tunneling. Two of these processes, (a) and (b), involve the interaction of electrons with a thermal bath of magnons on the right hand side of the junction and are responsible for transferring electrons in opposite di-

rections. The process (a) begins with a "electron on the left w ith wavevector  $k_{\rm L}\!=\!\!$  (k  $_{\rm L}^k$  ;  $k_{\rm L}^z$  ) [w ith occupation num – ber n<sub>I</sub> (k<sub>I</sub>)], which tunnels through the barrier into an interm ediate virtual " state on the right  $(k_R = (k_L^k; k_R^z))$ . Then, this electron ips spin by em itting a magnon with wavevectorq [this process is stimulated by the occupancy factor of therm alm agnon excitations  $1 + N_R(q)$ , and, thus, incorporates itself into the majority spin band on the right, provided the  $nal \# state (k^0 = k_R q)$  is not occupied [which has probability  $1 n_R (k_R q)$ ]. The process (b) is the reverse to the process (a). It begins with a # electron on the right with wavevector  $k^0 = k_R$ that absorbs a magnon, ips its spin and moves into a virtualm inority-spin state on the right. Then, it tunnels into an empty nal state in the majority spin band in the left reservoir. The balance between these two processes contributes to the total current as

$$I_{ab} = 4^{2} \frac{e^{\sum_{k=1}^{2} 1} d^{k_{L},k_{R}} d^{k_{L},k_{R}} d^{k_{L},k_{R}}}{1 e^{k_{L}} e^{k_{L}$$

where 
$$n_{L=R}$$
 (k) = [expf( $_k$   $_F^{L=R}$  g= $k_B$   $T_{L=R}$ ) + 1]  $^1$ ,  $_F^L$   $_F^R$  = eV,  $N_{L=R}$  (q) = [exp(! $_q$ = $k_B$   $T_{L=R}$ ) 1]  $^1$ , and  $T_{L=R}$  = T  $_T$ =2.

Two other processes shown in Figure 1 (c) and (d) involve em ission/absorption of magnons on the left hand side of the junction. Their contribution to the total current is

$$I_{cd} = 4^{\frac{2}{h}} \frac{e^{\sum_{k=1}^{L+1} X}}{e^{\sum_{k=1}^{L+1} k_{k} q}} (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) [e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}] (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) [e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}] (e^{\sum_{k=1}^{L+1} k_{k} k_{k} q}) ($$

A fler combining them together into an expression for the total current  $I = I_{ab} + I_{cd}$ , and, then, performing summation over wave numbers and integration over initial electron energies, we arrived at the following expression

$$I = +\frac{3}{4} \frac{G_P}{e} \frac{k_B T}{!_D} = [a eV bk_B T];$$
 (5)

where a = 3 (3=2) (3=2), b = (5=2) (5=2) (5=2), (x) is the gam ma function, and (x) is R iem ann's zeta function. Here, all properties of the interface are incorporated into a single parameter  $G_P$  which coincides with the linear conductance of the same mesoscopic junction in the P con guration. For a at, clean barrier of area A, where the parallel component of momentum is conserved upon tunneling, we consider the tunneling matrix element to have the form  $t_{k,k^0} = t_{k,k^0} t_{k}^2 v_k^z = L^2 t_{k}^{1=2}$ ,

which gives G  $_{\rm P}$  4  $^2$  (e $^2$ =h)  $\rm jt_{\rm J}^2$  (A  $_{+}$ =h $^2$ ) where  $\rm v_{L~(R)}^z$  is the perpendicular component of velocity on the left (right) side, L is the length of an electrode, t is the barrier transparency, and  $_{+}$  is the area of the maximal cross-section of the Ferm i surface of majority electrons in the plane parallel to the interface. When deriving Eq. (5), we also assumed a quadratic magnon dispersion, ! $_{\rm q}$  = D q $^2$ , and  $\rm k_B$  T  $_{\rm D}$ , where ! $_{\rm D}$  = D (6  $^2$ =v) $^{2-3}$  is the D ebye magnon energy, and v is the volume of a unit cell.

The thermopower coe cient S = V = T can be found by setting the total current in Eq. (5) to zero and determ ining the voltage created by the temperature di erence. As a result, the tunneling conductance Gp cancels from the nal answer, and, in the antiparallel con guration, SAP 0:64k =e.<sup>13</sup> In contrast to the AP con quration, magnon-assisted tunneling cannot contribute to the electron transfer between two electrodes in the P con guration, since both initial and nalelectron states should have the same spin polarization in order to belong to the majority bands in both of the reservoirs. As a result, the linear conductance of such a junction is form ed without the involvem ent of magnon-assisted processes, and the therm opowerm ay only appear due to the energy-dependent electron tunneling density of states, having the order of magnitude of Sp  $(k_B = e) (k_B T = F)$ .

A generalization to conventional ferrom agnetic m etals of the proposed theory of the magnon-assisted (ma) tunneling contribution to the therm opower yields

$$S_{AP}^{ma} = (k_B = e) g ; S_{P}^{ma} = 0;$$
 (6)

$$g = \frac{1:7}{!_{D}} = \frac{k_{B} T}{!_{D}} = ( \begin{array}{ccc} + & & )= & ; & \text{at} \\ ( \begin{array}{ccc} 2 & & 2 \end{array}) = ( \begin{array}{ccc} + & & ); & \text{di} \end{array}$$

is the area of the maximal cross-section of the Ferm i surface of majority/minority electrons in the plane parallel to the interface ( + > spin of localized m om ents, and ! D is the magnon bandwidth. The function g(T) is proportional to the fractional change in the net magnetization due to thermal m agnons (B loch's T  $^{3-2}$  law ) and the function is written for both a at, clean interface ('at') and a di usive tunnelbarrier (di '). This result was obtained after som e am endm ents to the above analysis were made. First, the linear conductance in the AP con guration is not suppressed because an elastic tunneling channel is opened between the majority band on one side and the minority band on the other, which reduces the therm opower. Secondly, for the AP con guration, in addition to the m agnon-assisted tunneling processes that enable transitions from majority initial to majority nal states via an interm ediate m inority state (as described already for the

halfm etallic case and shown in Fig. 1), one should take into account the possibility ofm agnon-assisted tunneling processes that enable transitions from m inority initial to m inority nal states via an interm ediate majority state. A transition via a majority (minority) interm ediate state results in the transfer of electrons in the same (opposite) direction as the net polarization transfer between two baths of magnons so that the additional processes partially compensate the thermally excited currents.

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The sign of the therm opower coe cient is specified for the electron (charge e) transfer process and under the assumption that the exchange between conduction band and core electrons has a ferrom agnetic sign. For antiferrom agnetic exchange, the sign of the therm opower would be opposite. One can verify this statement by taking into account that processes, described for example in Fig. 1 (a) and (b), would involve magnons on the opposite side of the junction, hence the current  $\rm I_{ab}$  would be determined by magnon occupation numbers N  $\rm I_L$  (q).